

2SD1516

Silicon NPN Epitaxial Planar Type

Power Amplifier, Power Switching

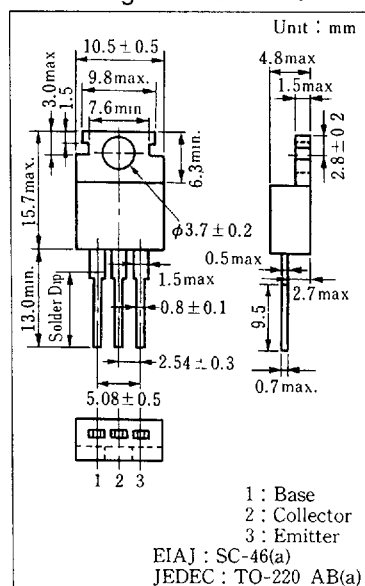
■ Features

- Low collector-emitter saturation voltage ($V_{CE(sat)}$)
- Good linearity of DC current gain (h_{FE})
- High collector current (I_C)
- High speed switching

■ Absolute Maximum Ratings ($T_c=25^\circ\text{C}$)

Item	Symbol	Value	Unit
Collector-base voltage	V_{CBO}	130	V
Collector-emitter voltage	V_{CEO}	80	V
Emitter-base voltage	V_{EBO}	7	V
Peak collector current	I_{CP}	5	A
Collector current	I_C	2	A
Collector power dissipation	$T_c=25^\circ\text{C}$	P_C	W
	$T_a=25^\circ\text{C}$	1 4	
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	$-55 \sim +150$	$^\circ\text{C}$

■ Package Dimensions

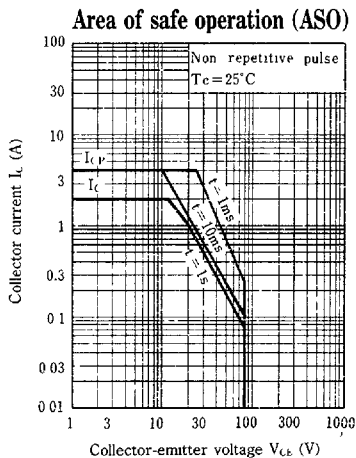
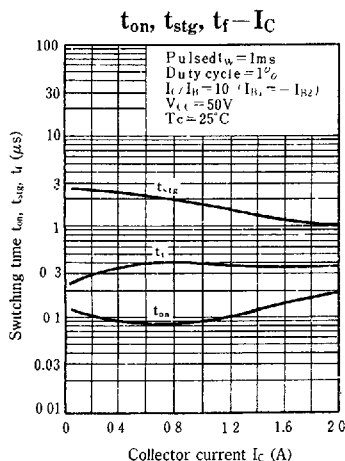
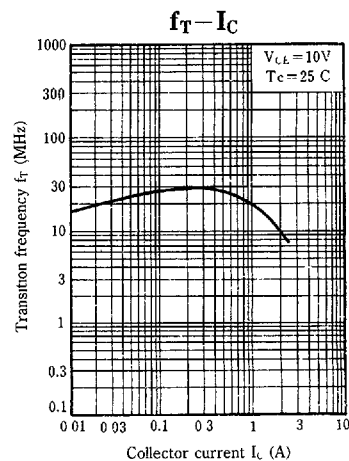
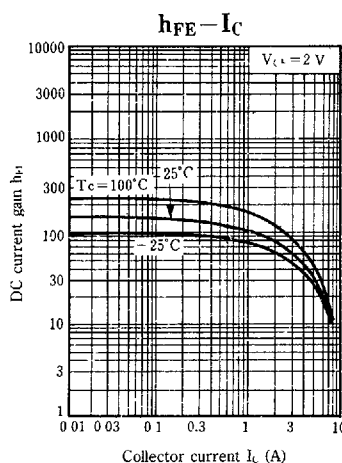
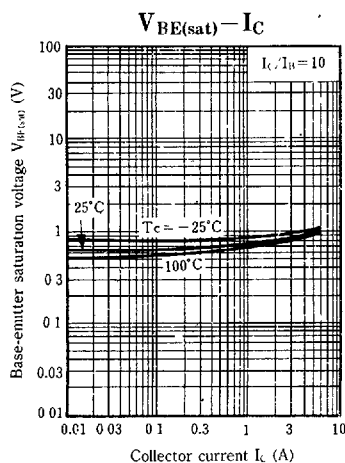
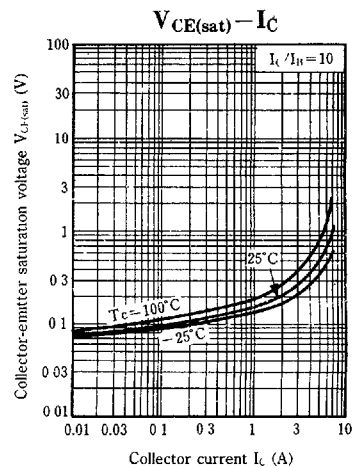
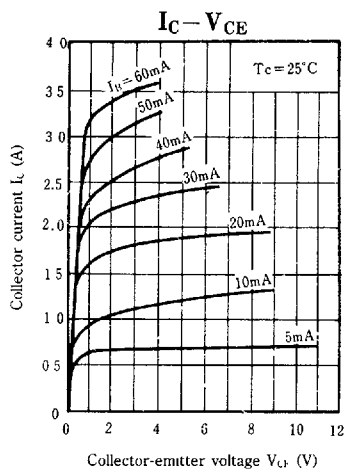
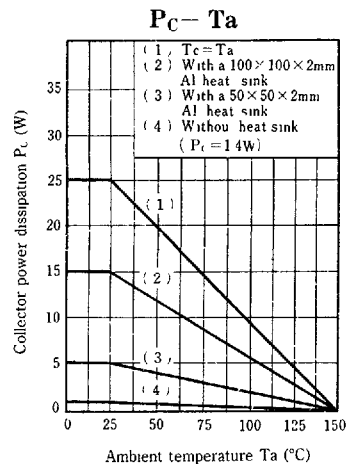


■ Electrical Characteristics ($T_c=25^\circ\text{C}$)

Item	Symbol	Condition	min.	typ.	max.	Unit
Collector cutoff current	I_{CBO}	$V_{CB}=100\text{ V}, I_E=0$			10	μA
Emitter cutoff current	I_{EBO}	$V_{EB}=5\text{ V}, I_C=0$			50	μA
Collector-emitter voltage	V_{CEO}	$I_C=10\text{ mA}, I_B=0$	80			V
DC current gain	h_{FE1}^*	$V_{CE}=2\text{ V}, I_C=0.1\text{ A}$	45			
	h_{FE2}	$V_{CE}=2\text{ V}, I_C=0.5\text{ A}$	60		260	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=2\text{ A}, I_B=0.1\text{ A}$			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=2\text{ A}, I_B=0.1\text{ A}$			1.5	V
Transition frequency	f_T	$V_{CE}=10\text{ V}, I_C=0.5\text{ A}, f=10\text{ MHz}$		25		MHz
Turn-on time	t_{on}	$I_C=0.5\text{ A}, I_{B1}=50\text{ mA}, I_{B2}=-50\text{ mA}$ $V_{CC}=50\text{ V}$		0.1		μs
Storage time	t_{stg}			2.5		μs
Fall time	t_f			0.3		μs

* h_{FE1} Classifications

Class	R	Q	P
h_{FE1}	60~120	90~180	130~260



Note) Refer to P.860 (on 2SD1770/A) for $R_{th(t)} - t$ characteristics